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Stocking Distributor

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[Diodes Incorporated](#)

[DMG6968UTS-13](#)

For any questions, you can email us directly:

sales@integrated-circuit.com



DMG6968UTS

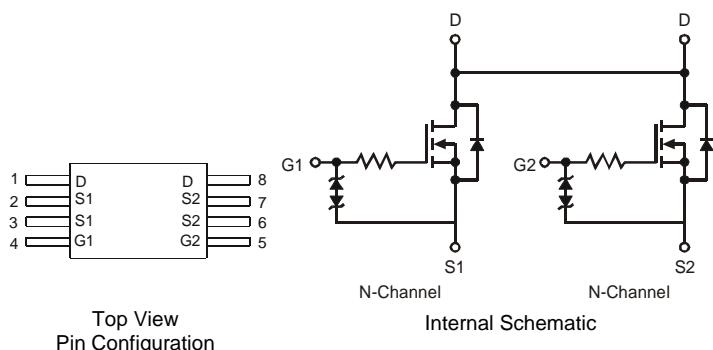
DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)
- **ESD Protected Up To 2kV**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: TSSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.039 grams (approximate)



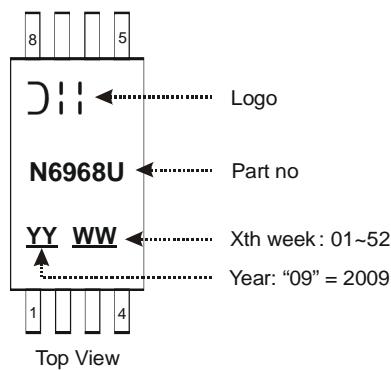
Ordering Information (Note 3)

Part Number	Case	Packaging
DMG6968UTS-13	TSSOP-8	2500 / 13" Tape & Reel

Notes:

1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information





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Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D	5.2	A
		$T_A = 70^\circ\text{C}$		3.5	
Pulsed Drain Current			I_{DM}	30	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	1.0	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

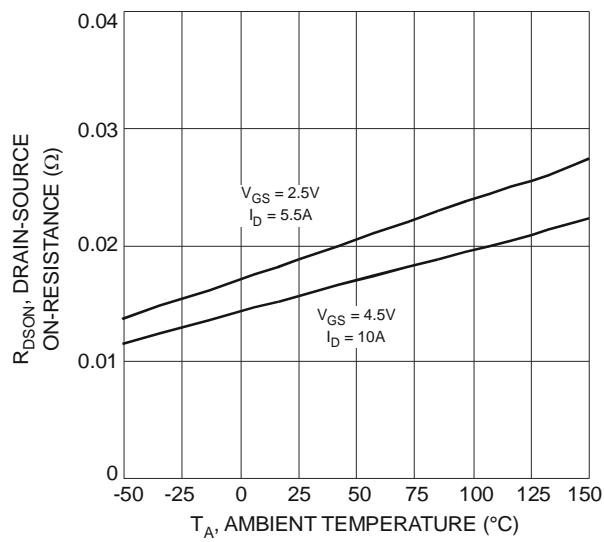
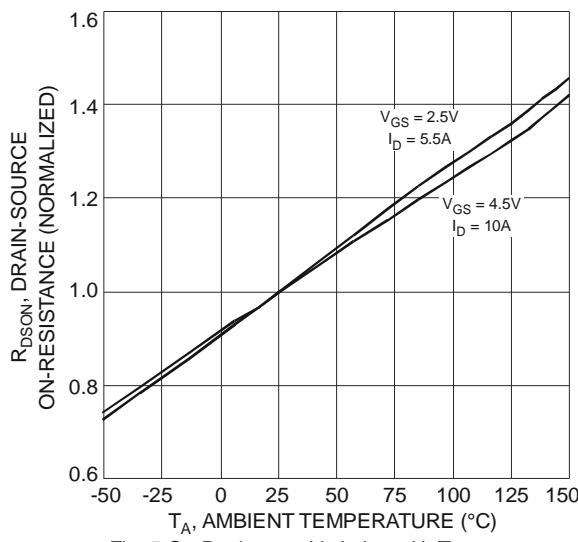
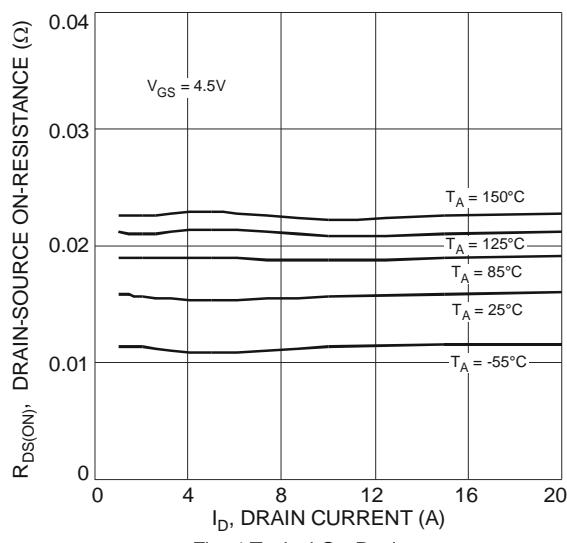
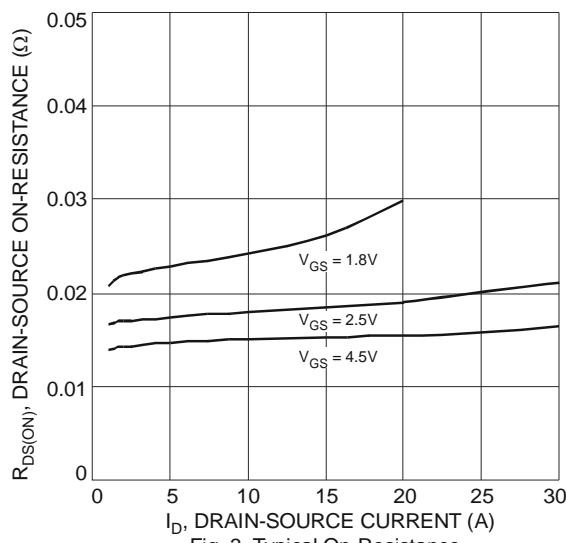
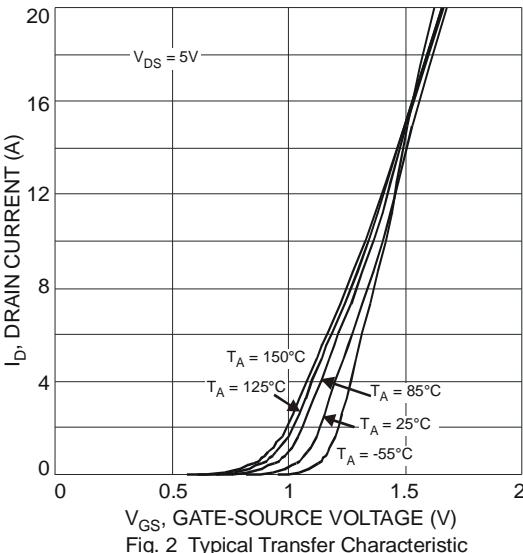
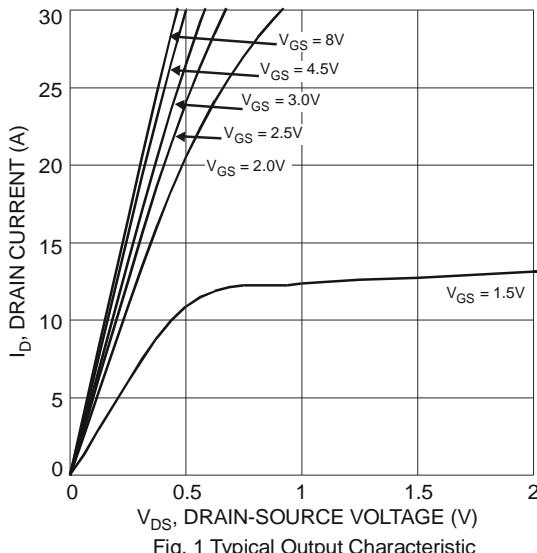
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
Gate-Source Breakdown Voltage	BV_{SGS}	± 12	-	-	V	$V_{DS} = 0V, I_G = \pm 250\mu\text{A}$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(\text{th})}$	0.35	-	0.95	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	-	18	23	$\text{m}\Omega$	$V_{GS} = 4.5V, I_D = 6.5\text{A}$
		-	21	27		$V_{GS} = 2.5V, I_D = 5.5\text{A}$
		-	26	34		$V_{GS} = 1.8V, I_D = 3.5\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	-	13	-	S	$V_{DS} = 5V, I_D = 5\text{A}$
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	-	143	-	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	74	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	29	-	pF	
Gate Resistance	R_g	-	202	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge	Q_g	-	8.8	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5\text{A}$
Gate-Source Charge	Q_{gs}	-	1.4	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.0	-	nC	
Turn-On Delay Time	$t_{D(\text{on})}$	-	53	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V, R_L = 10\Omega, R_G = 6\Omega$
Turn-On Rise Time	t_r	-	78	-	ns	
Turn-Off Delay Time	$t_{D(\text{off})}$	-	562	-	ns	
Turn-Off Fall Time	t_f	-	234	-	ns	

Notes: 4. Device mounted on FR-4 PCB.
 5. Short duration pulse test used to minimize self-heating effect.



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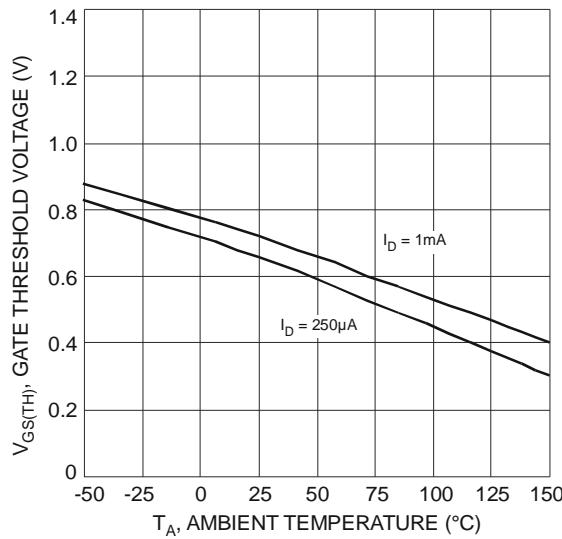


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

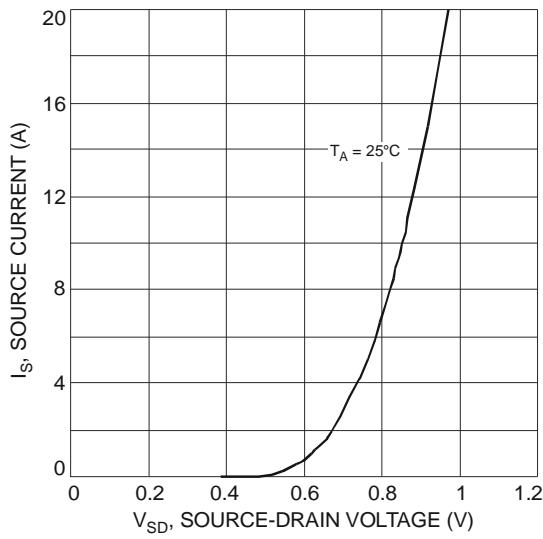


Fig. 8 Diode Forward Voltage vs. Current

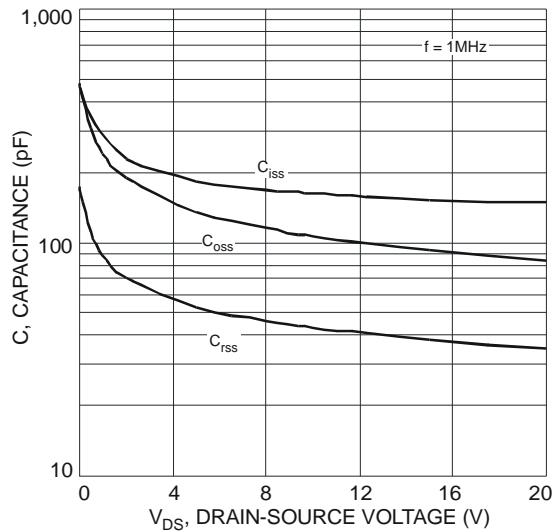


Fig. 9 Typical Total Capacitance

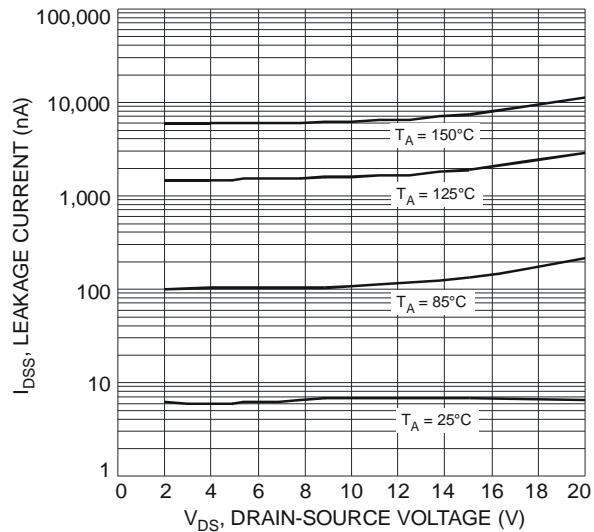


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

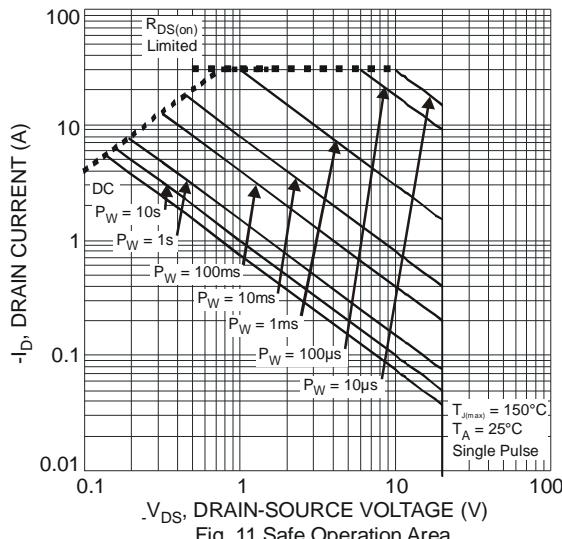


Fig. 11 Safe Operation Area

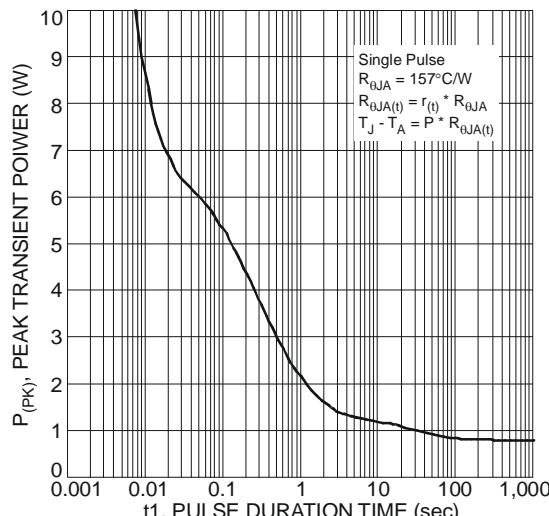


Fig. 12 Single Pulse Maximum Power Dissipation



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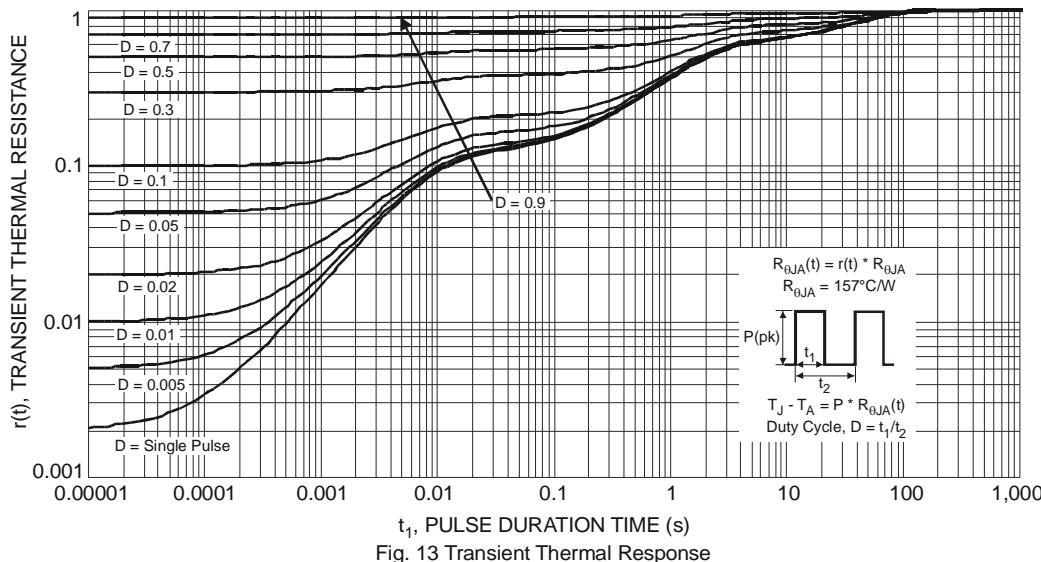
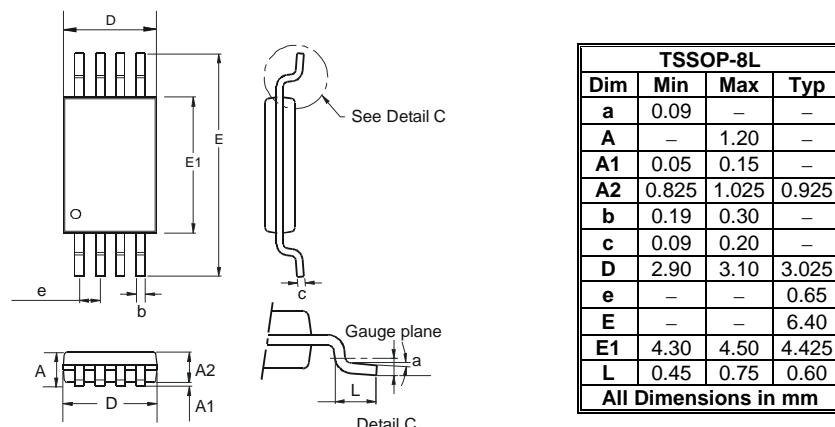
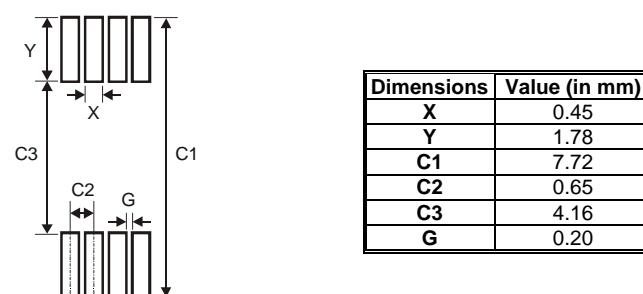


Fig. 13 Transient Thermal Response

Package Outline Dimensions



Suggested Pad Layout



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